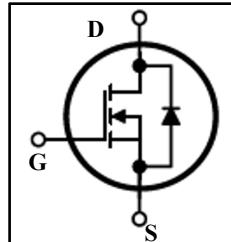
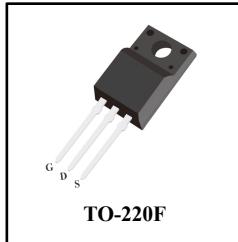


**FEATURES**

- $BV_{DSS}$ : 650V,  $I_D=7A$
- $R_{DS(on)}$  : 1.4Ω(Max) @ $V_{GS}=10V$
- Very Low FOM ( $R_{DS(on)} * Q_g$ )
- Excellent stability and uniformity

**APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- AC to DC Converters


**Ordering Information**

Type NO.	Marking	Package Code
MPVA7N65F	MPVA7N65F	TO-220F

**Absolute Maximum Ratings**  $T_C = 25^\circ C$ , unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	650	V
Continuous Drain Current	$I_D$	7	A
Pulsed Drain Current (note1)	$I_{DM}$	28	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	230	mJ
Avalanche Current (note1)	$I_{AR}$	4	A
Repetitive Avalanche Energy (note1)	$E_{AR}$	21.7	mJ
Power Dissipation ( $T_C = 25^\circ C$ )	$P_D$	35	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	°C

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	1.98	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5	



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# MPVA7N65F

## Power MOSFET

### Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted

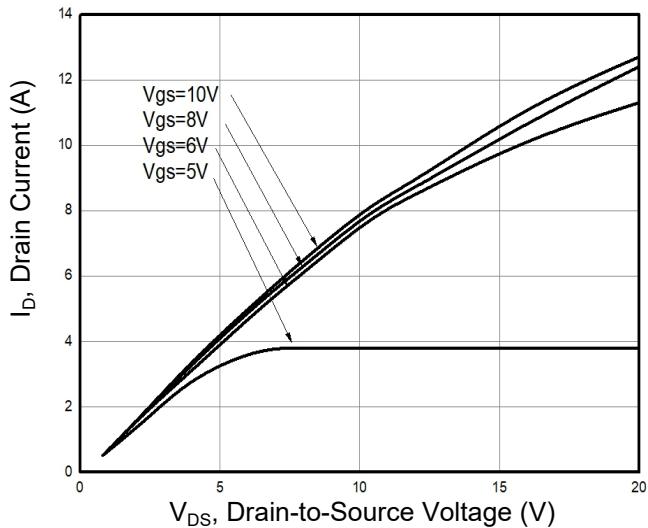
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	650	--	--	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 650\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
Gate-Source Leakage	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 30\text{V}$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	--	4.0	V
Drain-Source On-Resistance (Note4)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 3.5\text{A}$	--	1.1	1.4	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	1178	--	pF
Output Capacitance	$C_{\text{oss}}$		--	89	--	
Reverse Transfer Capacitance	$C_{\text{rss}}$		--	10	--	
Total Gate Charge	$Q_g$	$V_{\text{DD}} = 400\text{V}, I_D = 7.0\text{A}, V_{\text{GS}} = 10\text{V}$	--	19	--	nC
Gate-Source Charge	$Q_{\text{gs}}$		--	5	--	
Gate-Drain Charge	$Q_{\text{gd}}$		--	5	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 325\text{V}, I_D = 7.0\text{A}, R_G = 25\Omega$	--	33	--	ns
Turn-on Rise Time	$t_r$		--	50	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	42	--	
Turn-off Fall Time	$t_f$		--	35	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	7	A
Pulsed Diode Forward Current	$I_{\text{SM}}$		--	--	28	
Body Diode Voltage	$V_{\text{SD}}$	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 7.0\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.4	V
Reverse Recovery Time	$t_{\text{rr}}$	$V_R = 400\text{V}, I_F = 7.0\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	365	--	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		--	3.4	--	$\mu\text{C}$

### Notes

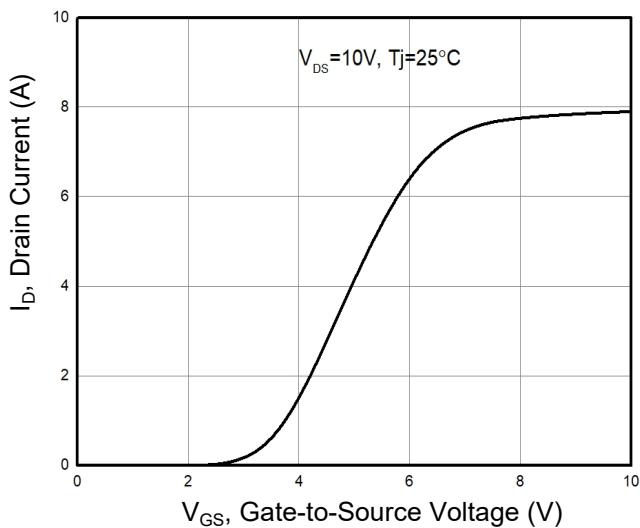
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 10\text{mH}, V_{\text{DD}} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$
4. Essentially independent of operating temperature

Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

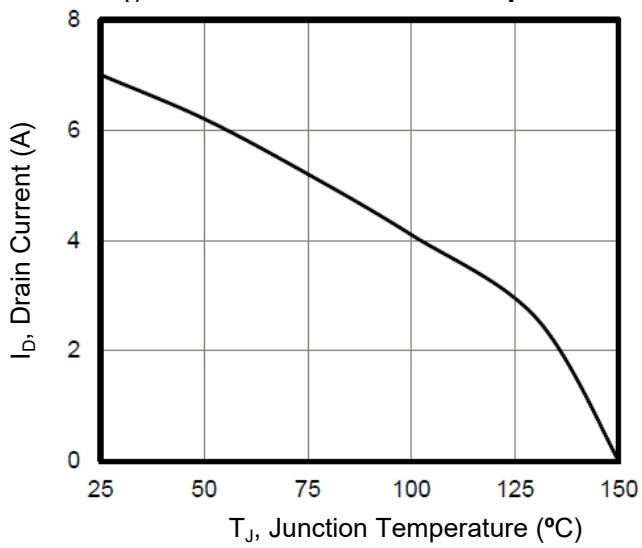
**Figure 1. Output Characteristics**



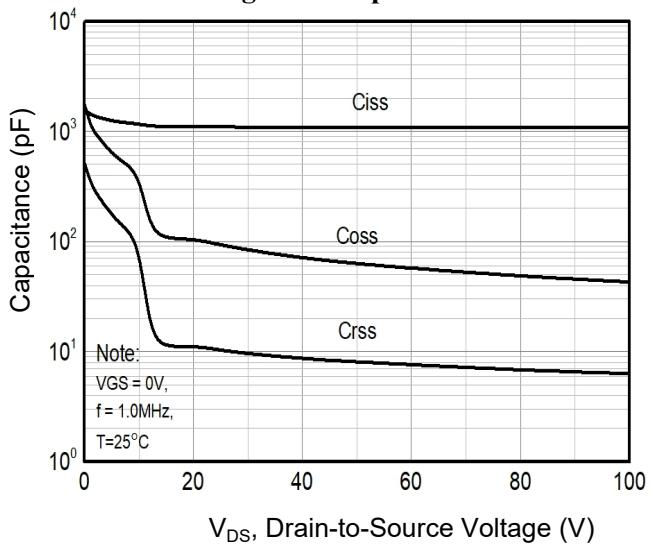
**Figure 2. Transfer Characteristics**



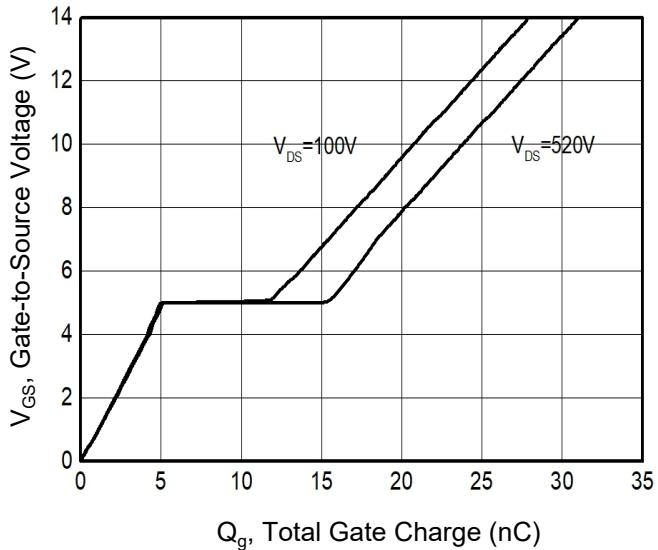
**Figure 3. Drain Current vs. Temperature**



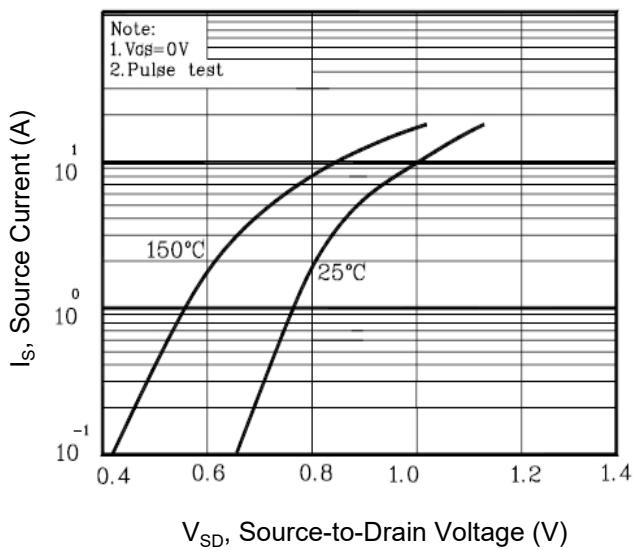
**Figure 4. Capacitance**



**Figure 5. Gate Charge**

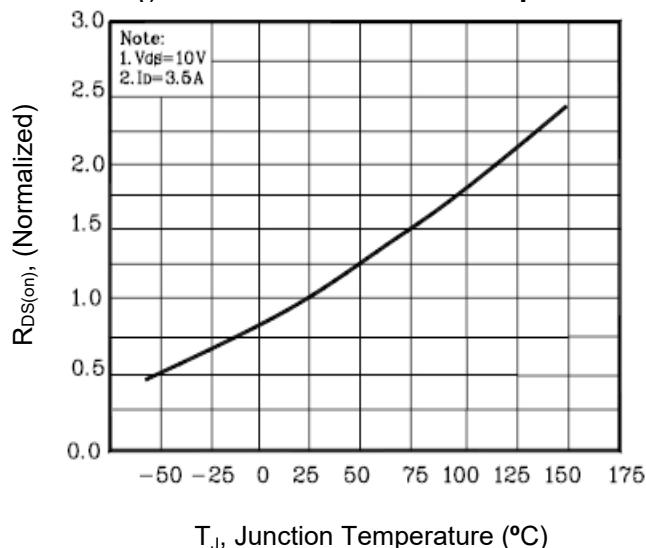


**Figure 6. Body Diode Forward Voltage**

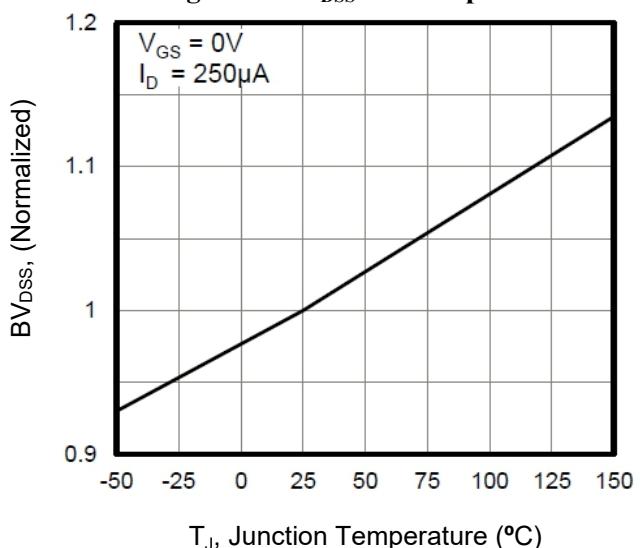


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

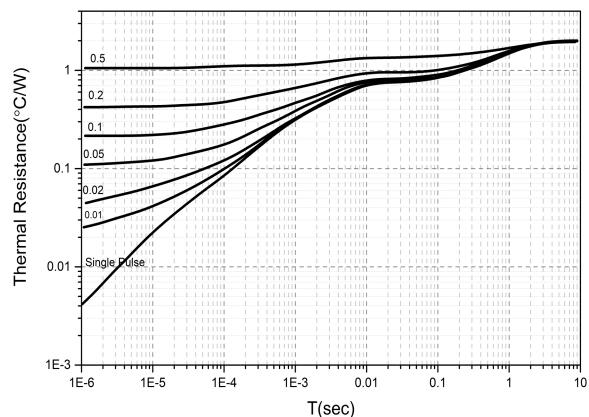
**Figure 7. On-Resistance vs. Temperature**

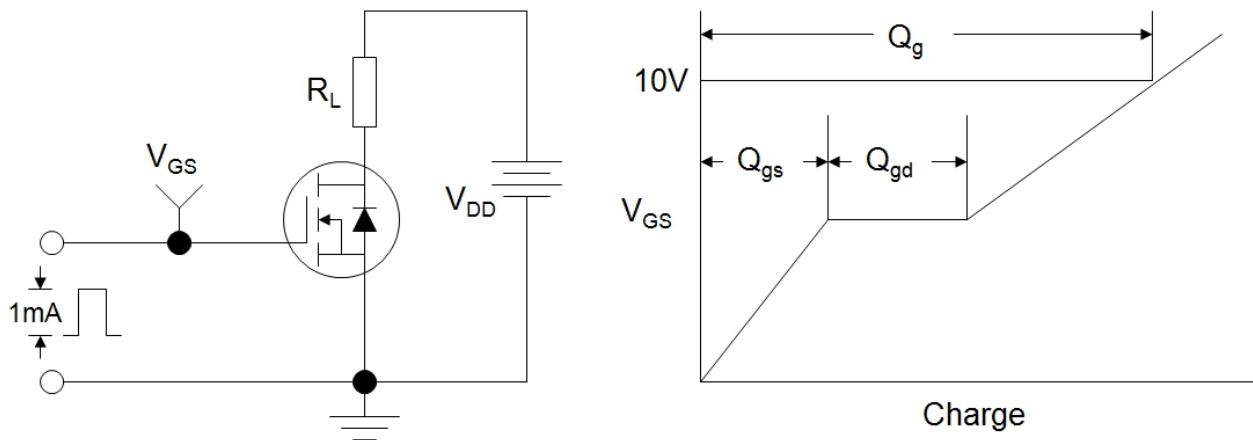
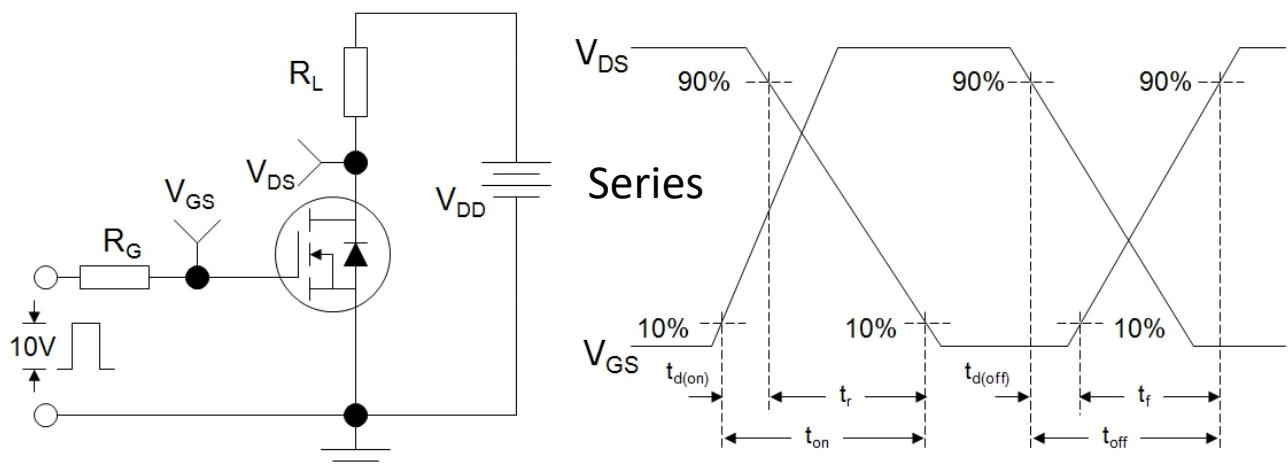
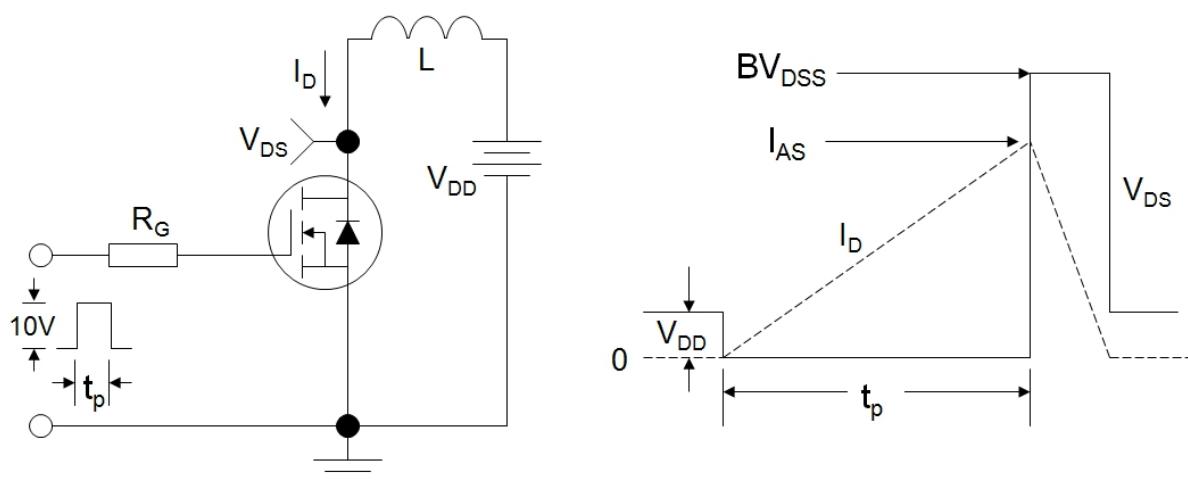


**Figure 8.  $\text{BV}_{DSS}$  vs. Temperature**



**Figure 9. Transient Thermal Impedance**

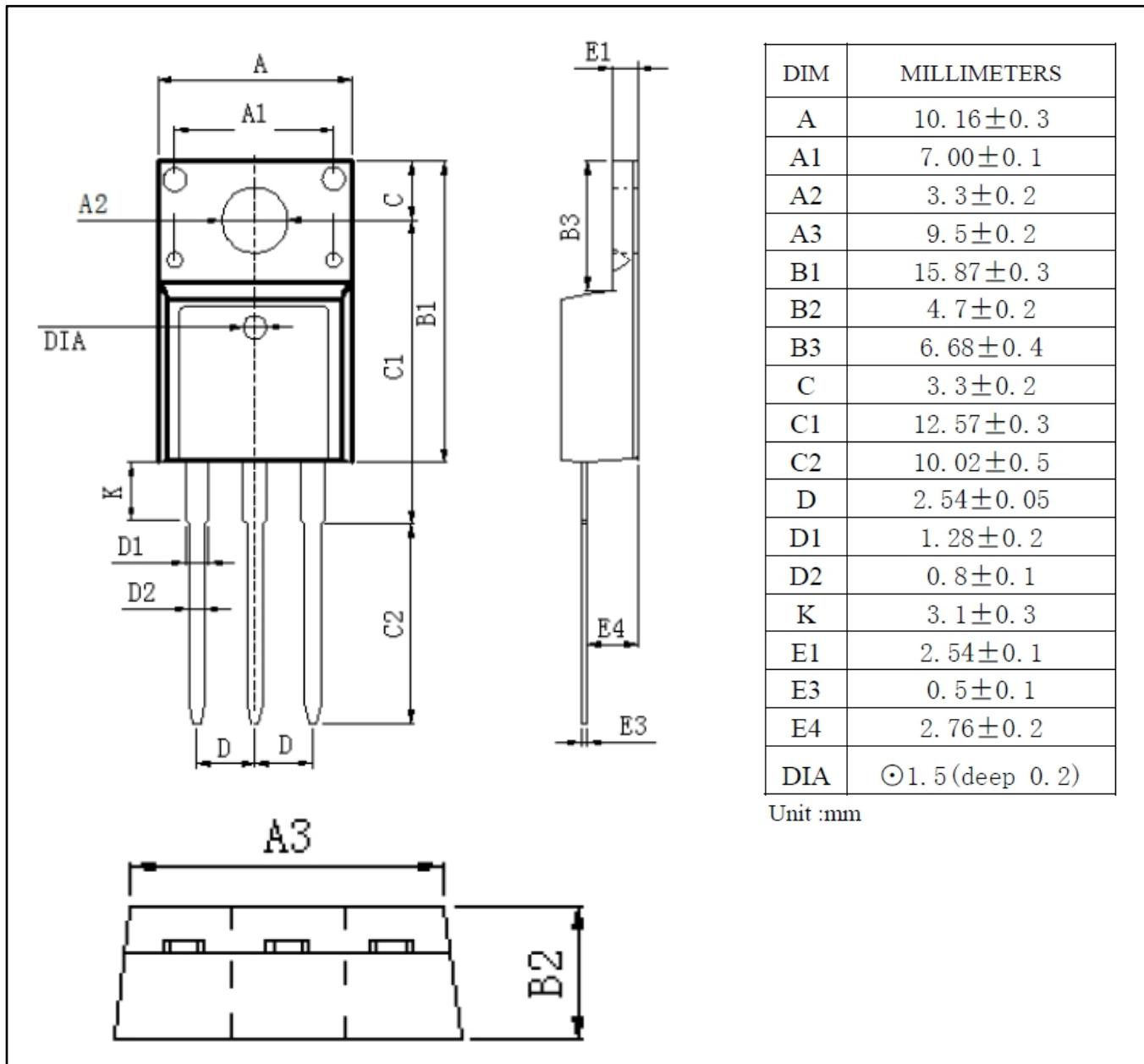


**Figure A: Gate Charge Test Circuit and Waveform**

**Figure B: Resistive Switching Test Circuit and Waveform**

**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**


## Outline Dimension

Unit: mm

### TO-220F



单击下面可查看定价，库存，交付和生命周期等信息

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